

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP721F

OFFICE MACHINE
SWITCHING POWER SUPPLY

Unit in mm

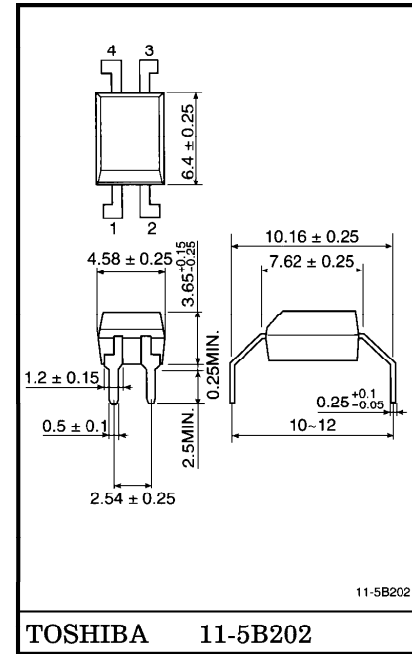
The TOSHIBA TLP721F consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP.

All parameters are tested to the specification of TLP721.
(both condition and limits)

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
Rank GB : 100% (Min.)

	MADE IN JAPAN		MADE IN THAILAND	
UL Recognized	E67349	*1	E152349	*1
BSI Approved	7364, 7365	*2	7364, 7365	*2
SEMKO Approved	9325163 9522142	*3 *3	9609169	*4

- *1 UL1577
- *2 BS EN60065 : 1994, BS EN60950 : 1992
- *3 SS EN4330784
- *4 SS EN60950



Weight : 0.28g

- Option (D4) type VDE Approved

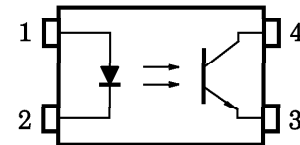
	MADE IN JAPAN	MADE IN THAILAND
VDE Approved	74285, 91835	91868
Maximum Operating Insulation Voltage	890, 1130Vpk	1130Vpk
Highest Permissible Over Voltage	6000, 8000Vpk	8000Vpk

*5 VDE0884 / 06.92

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- Creepage Distance : 8.0mm (Min.)
- Clearance : 8.0mm (Min.)
- Internal Creepage Path : 4.0mm (Min.)
- Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
 DIN 57 804.VDE0804 / 1.83
 DIN IEC65 / VDE0860 / 8.81
 DIN IEC380 / VDE0806 / 8.81
 DIN IEC435 / VDE0805 / Draft Nov.84
 DIN IEC601T1 / VDE0750T1 / 5.82
 BS7002 : 1989 (EN60950)

PIN CONFIGURATION (TOP VIEW)



- 1. ANODE
- 2. CATHODE
- 3. EMITTER
- 4. COLLECTOR

961001EBC2

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● Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

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